BLF6G20-45

UHF power LDMOS transistor

Rev. 01 — 20 February 2006 Objective data sheet

1. Product profile

1.1 General description

45 W LDMOS power transistor for base station applications at frequencies from 1800 MHz to 2000 MHz.

Table 1: Typical performance

RF performance at T_{case} = 25 °C in a common source class-AB production test circuit.

Mode of operation	f (MHz)	V_{DS} (V)	$P_{L(AV)}$ (W)	G_p (dB)	η_D (%)	ACPR (dBc)
2-carrier W-CDMA	1805 to 1880	28	2.5	17	14	–50 [1]

[1] Test signal: 3GPP; test model 1; 64 DPCH; PAR = 7.5 dB at 0.01 % probability on CCDF per carrier; carrier spacing 5 MHz

CAUTION

This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features

- Typical 2-carrier W-CDMA performance at frequencies of 1805 MHz and 1880 MHz, a supply voltage of 28 V and an I_{Dq} of 350 mA:
  - Average output power = 2.5 W
  - Power gain = 17 dB (typ)
  - Efficiency = 14 %
  - ACPR = –50 dBc
- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (1800 MHz to 2000 MHz)
- Internally matched for ease of use

1.3 Applications

- RF power amplifiers for W-CDMA base stations and multi carrier applications in the 1800 MHz to 2000 MHz frequency range.

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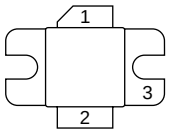
2. Pinning information

Table 2: Pinning

Pin	Description	Simplified outline	Symbol
1	drain		<tbd>
2	gate		
3	source [1]		

[1] Connected to flange

3. Ordering information

Table 3: Ordering information

Type number	Package		
	Name	Description	Version
BLF6G20-45	-	flanged ceramic package; 2 mounting holes; 2 leads	SOT608A

4. Limiting values

Table 4: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		–0.5	+13	V
I_D	drain current		-	<tbd>	A
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		-	225	°C

5. Thermal characteristics

Table 5: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j\text{-}case)}$	thermal resistance from junction to case	T_{case} = 80 °C; P_L = <tbd>	<tbd>	<tbd>	<tbd>	K/W

6. Characteristics

Table 6: Characteristics

T_j = 25 °C per section; unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 0.5 mA	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_D = 60 mA	**<tbd>**	1.6	**<tbd>**	V
V_{GSq}	gate-source quiescent voltage	V_{DS} = 28 V; I_D = 300 mA	**<tbd>**	2	**<tbd>**	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 28 V	-	-	1.5	µA
I_{DSX}	drain cut-off current	V_{GS} = $V_{GS(th)}$ + 3.75 V; V_{DS} = 10 V	9	11	-	A
I_{GSS}	gate leakage current	V_{GS} = 13 V; V_{DS} = 0 V	-	-	150	nA
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 3 A	-	**<tbd>**	-	S
$R_{DS(on)}$	drain-source on-state resistance	V_{GS} = $V_{GS(th)}$ + 3.75 V; I_D = 2.1 A	-	0.25	**<tbd>**	Ω
C_{rs}	feedback capacitance	V_{GS} = 0 V; V_{DS} = 28 V; f = 1 MHz	-	**<tbd>**	-	pF

7. Application information

Table 7: Application information

Mode of operation: 2-carrier W-CDMA; PAR 7.5 dB at 0.01 % probability on CCDF; 3GPP test model 1; 1-64 PDPCH; f_1 = 1807.5 MHz; f_2 = 1812.5 MHz; f_3 = 1872.5 MHz; f_4 = 1877.5 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 2 × 900 mA; T_{case} = 25 °C; unless otherwise specified; in a class-AB production test circuit

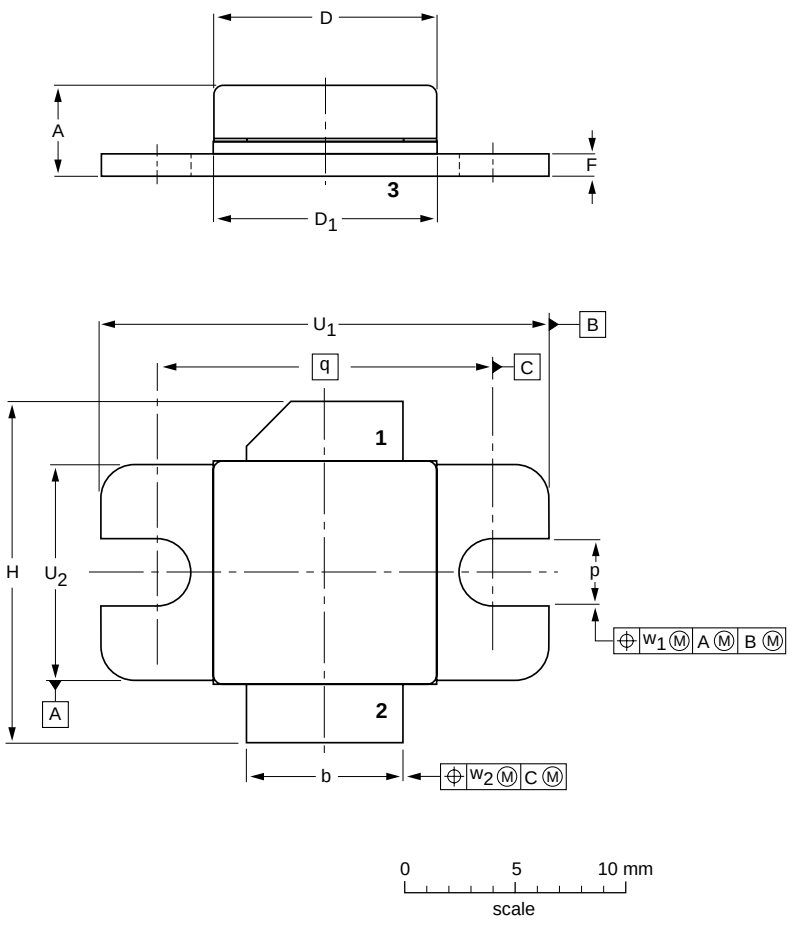
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$P_{L(AV)}$	average output power		-	2.5	-	W
G_p	power gain	$P_{L(AV)}$ = 2.5 W	**<tbd>**	17	-	dB
η_D	drain efficiency	$P_{L(AV)}$ = 2.5 W	**<tbd>**	14	-	%
IMD3	third order intermodulation distortion	$P_{L(AV)}$ = 2.5 W	-	**<tbd>**	**<tbd>**	dBc
ACPR	adjacent channel power ratio	$P_{L(AV)}$ = 2.5 W	-	–50	**<tbd>**	dBc

7.1 Ruggedness in class-AB operation

The BLF6G20-45 is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq} = 350 mA; P_L = 45 W (CW); f = 1880 MHz.

8. Package outline

Flanged ceramic package; 2 mounting holes; 2 leads **SOT608A**



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D_1	E	E_1	F	H	p	Q	q	U_1	U_2	w_1	w_2
mm	4.62 3.76	7.24 6.99	0.15 0.10	10.21 10.01	10.29 10.03	10.21 10.01	10.29 10.03	1.14 0.89	15.75 14.73	3.30 2.92	1.70 1.35	15.24	20.45 20.19	9.91 9.65	0.25	0.51
inches	0.182 0.148	0.285 0.275	0.006 0.004	0.402 0.394	0.405 0.395	0.402 0.394	0.405 0.395	0.045 0.035	0.620 0.580	0.130 0.115	0.067 0.053	0.600	0.805 0.795	0.390 0.380	0.010	0.020

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT608A						~~01-02-22~~ 02-02-11

Fig 1. Package outline SOT608A

9. Abbreviations

Table 8: Abbreviations

Acronym	Description
3GPP	Third Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
LDMOS	Laterally Diffused Metal Oxide Semiconductor
PAR	Peak-to-Average power Ratio
PDPCH	transmission Power of the Dedicated Physical CHannel
RF	Radio Frequency
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

10. Revision history

Table 9: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
BLF6G20-45_1	20060220	Objective data sheet	-	-	-

11. Data sheet status

Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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